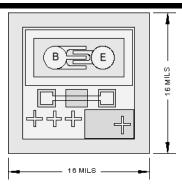


Chip Type 2C2857 Geometry 0011 **Polarity NPN** 

Data Sheet No. 2C2857

**Generic Packaged Part:** 

2N2857



**Request Quotation** 

Chip type 2C2857 by Semicoa Semiconductors provides performance similar to these devices.

## Part Numbers:

2N2857, 2N2857UB, SD2857, SD2857F, SQ2857, SQ2857F

**Product Summary:** 

**APPLICATIONS:** Designed for use in high-gain, low noise amplifier, oscillator, mixer and UHF converters.

## Features: ft = 1.2 GHz (typ) at 5 mA/6V

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Mec	hanical Sp	ecificati	ons		
Metallization		Al - 15 kÅ min.			
		Au - 6.5 kÅ nom.			
Bonding Pad Size			2.3 mils x 2.3 mils		
			2.3 mils x 2.3 mils		
Die Thickness		8 mils nominal			
Chip Area		16 mils x 16 mils			
Top Surface		Silox Passivated			
El			S		
Test co	nditions	Min	Max	Unit	
I <sub>C</sub> = 3.0 mA		15		V dc	
I <sub>C</sub> = 1.0 μA					
I <sub>C</sub> = 1	.0 μA	30		V dc	
	.0 μΑ 10 μΑ	30 2.5		V dc V dc	
	lization Pad Size nickness Area Surface Ele Test co I <sub>C</sub> = 3	$\begin{tabular}{ c c c c } \hline Top \\ \hline Backside \\ \hline Backside \\ \hline Emitter \\ \hline Base \\ $	$\begin{tabular}{ c c c c c } \hline Top & & & & & & & & & & & & & & & & & & &$	IzationBacksideAu - 6.5 kÅrPad SizeEmitter2.3 mils x 2.3icknessBase2.3 mils x 2.3ickness8 mils nominalArea16 mils x 16 milsSurfaceSilox PassivatedElectrical Characteristics $T_A = 25^{\circ}C$ Test conditions $I_c = 3.0 \text{ mA}$ 15	

 $I_{\rm C}$  = 3.0 mA dc,  $V_{\rm CE}$  = 1.0 V Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width of less than 300 µs, duty cycle less than 2%.

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h<sub>FE</sub>